

Supplementary Information

Molecular beam epitaxy of InAs quantum wells on InP(001) for high mobility two-dimensional electron gases

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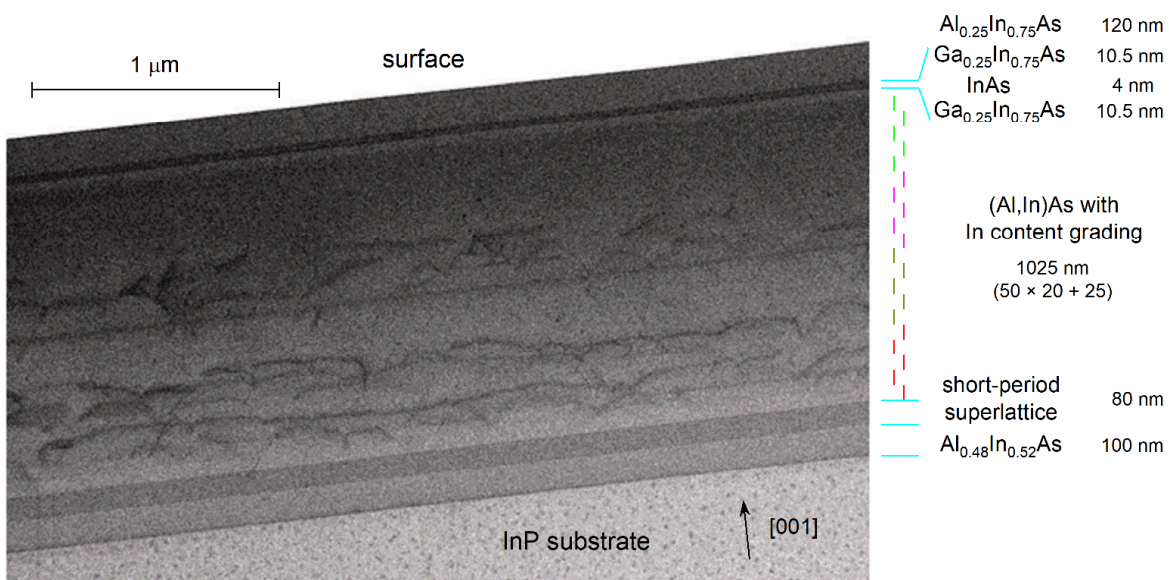


Fig. S1. Z-contrast scanning transmission electron microscopy image of heterostructure grown on InP(001).

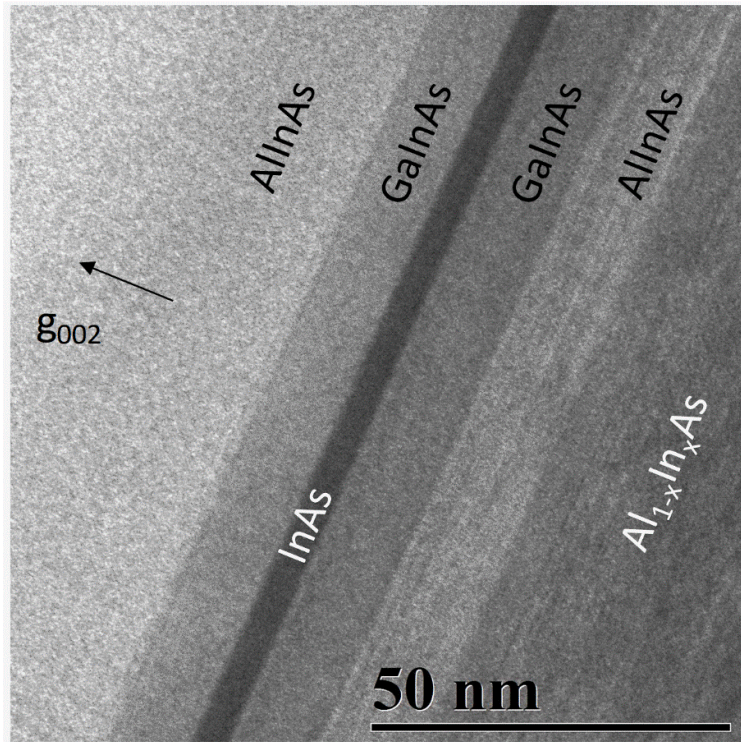


Fig. S2. Bright-field transmission electron microscopy image in 002 two beam condition. The image is sensitive to the difference in atomic scattering factors between group III and group V atoms.